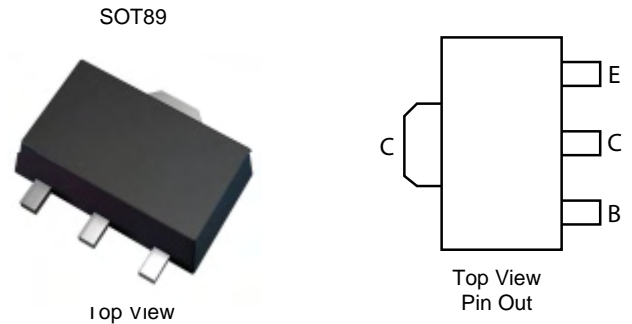


60V PNP LOW SATURATION MEDIUM POWER TRANSISTOR

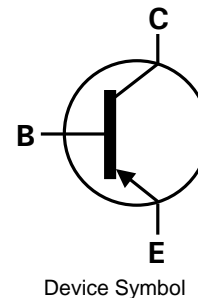
Features

- $V_{CE0} > -60V$
- $I_C = -4.3A$ high continuous current
- $R_{SAT} = 32m\Omega$ for a low equivalent On-Resistance
- Low saturation voltage $V_{CE(sat)} < -65mV$ @ $I_C = -1A$
- h_{FE} specified up to $-10A$ for high current gain hold up
- Complementary NPN type: PBSS304NX
- **Lead-Free Finish; RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **PPAP capable (Note 4)**



Application

- Emergency lighting circuits
- Motor driving (including DC fans)
- Backlight inverters
- Power switches
- Gate driving MOSFETs and IGBTs



Mechanical Data

- Case: SOT89
- Case material: molded plastic. "Green" molding compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.05 grams (Approximate)

Maximum Ratings (@ $T_A = +25^\circ C$, unless otherwise specified.)

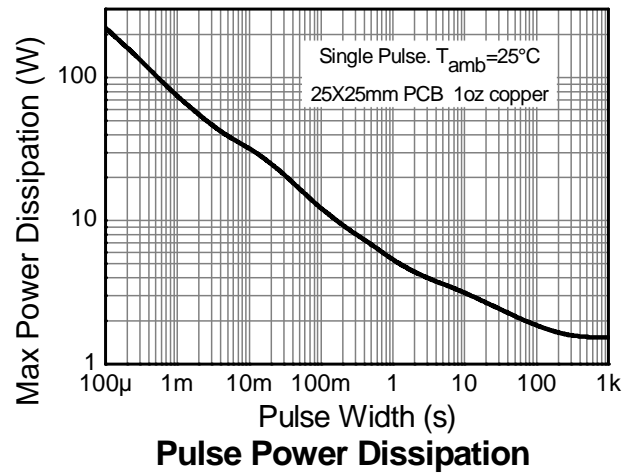
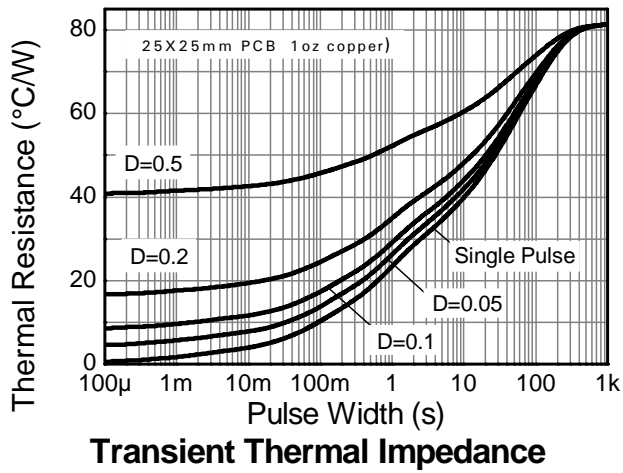
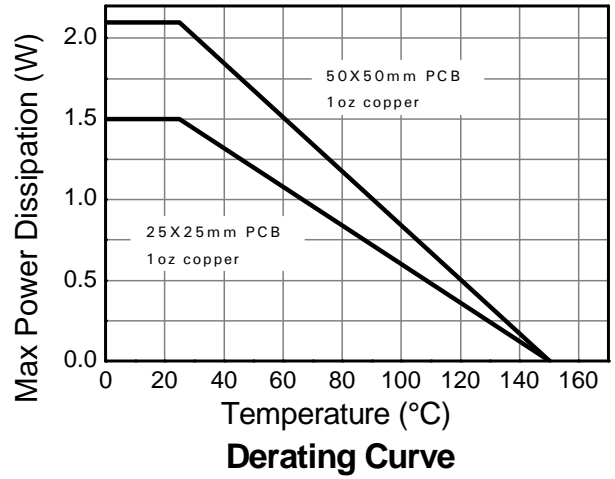
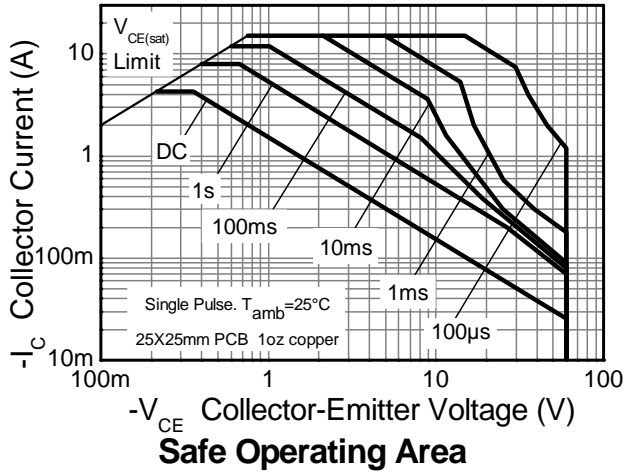
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	I_C	-4.3	A
Peak Pulse Current	I_{CM}	-15	A

Thermal Characteristics (@ $T_A = +25^\circ C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_D	1.5	W
Linear derating factor		12	mW/ $^\circ C$
Power Dissipation (Note 7)	P_D	2.1	W
Linear derating factor		16.8	mW/ $^\circ C$
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	83	$^\circ C/W$
Thermal Resistance, Junction to Ambient (Note 7)	$R_{\theta JA}$	60	$^\circ C/W$
Thermal Resistance, Junction to Leads (Note 8)	$R_{\theta JL}$	3.23	$^\circ C/W$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$

- Notes:
6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; device measured when operating in steady state condition.
 7. Same as note (6), except the device is mounted on 50mm X 50mm single sided 1oz weight copper.
 8. Thermal resistance from junction to solder-point (on the exposed collector pad).

Thermal Characteristics and Derating Information

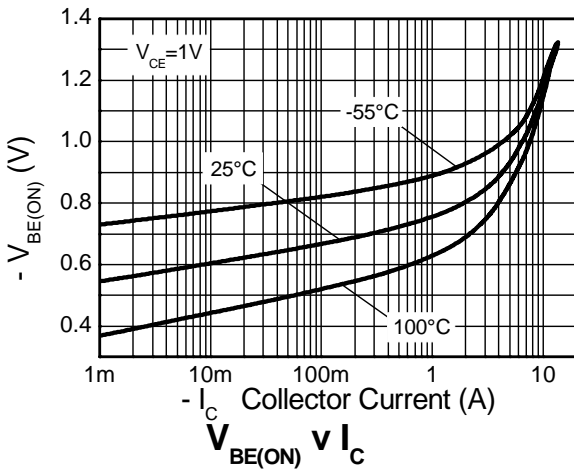
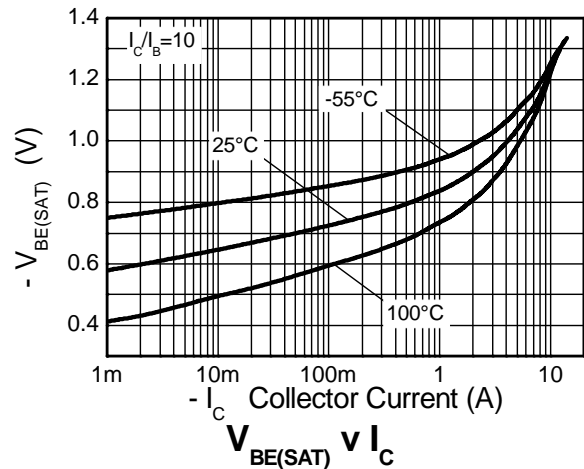
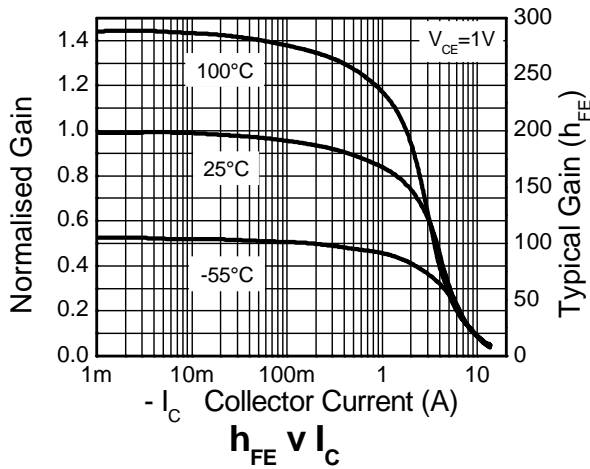
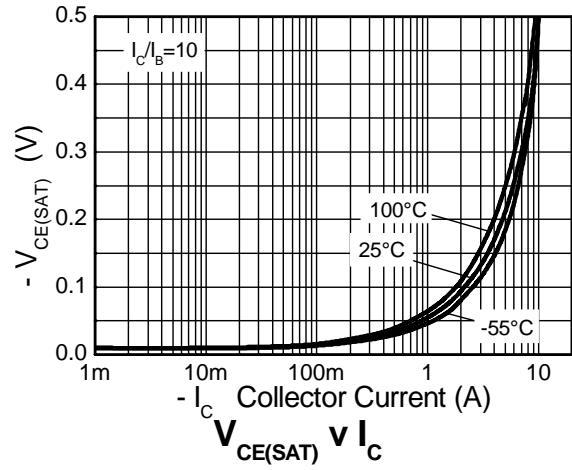
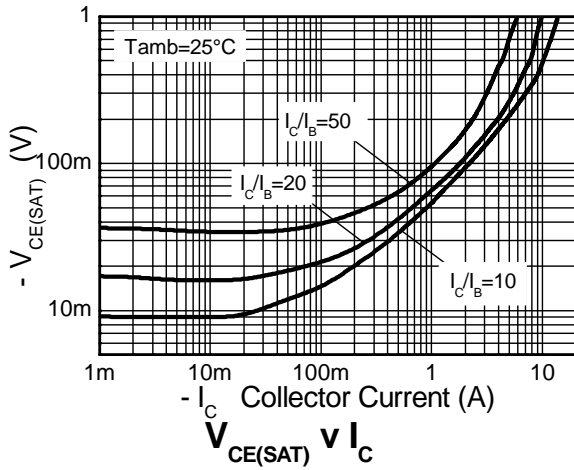


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-100	-120	-	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Notes 9)	BV _{CER}	-100	-120	-	V	I _C = -1μA, R _B ≤ 1kΩ
Collector-Emitter Breakdown Voltage (Notes 9)	BV _{CEO}	-60	-80	-	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.1	-	V	I _E = -100μA
Collector Cutoff Current	I _{CBO}	-	< -1	-20 -500	nA nA	V _{CB} = -80V V _{CB} = -80V, T _A = +100°C
Collector Cutoff Current	I _{CER} R ≤ 1kΩ	-	< -1	-20 -500	nA nA	V _{CB} = -80V V _{CB} = -80V, T _A = +100°C
Emitter Cutoff Current	I _{EBO}	-	< -1	-10	nA	V _{EB} = -6V
DC current transfer Static ratio (Notes 9)	h _{FE}	100 100 45 10	250 200 90 25	300		I _C = -10mA, V _{CE} = -1V I _C = -2A, V _{CE} = -1V I _C = -5A, V _{CE} = -1V I _C = -10A, V _{CE} = -1V
Collector-Emitter Saturation Voltage (Notes 9)	V _{CE(sat)}	-	-14 -50 -75 -160	-20 -65 -110 -215	mV	I _C = -100mA, I _B = -10mA I _C = -1A, I _B = -100mA I _C = -2A, I _B = -200mA I _C = -5A, I _B = -500mA
Base-Emitter Saturation Voltage (Notes 9)	V _{BE(sat)}	-	-950	-1050	mV	I _C = -5A, I _B = -500mA
Base-Emitter Turn-on Voltage (Notes 9)	V _{BE(on)}	-	-840	-950	mV	I _C = -5A, V _{CE} = -1V
Transitional Frequency (Notes 9)	f _T	-	120	-	MHz	I _C = -100mA, V _{CE} = -10V, f = 50MHz
Output capacitance	C _{obo}	-	48	-	pF	V _{CB} = -10V, f = 1MHz,
Switching Time	t _{ON}	-	39	-	ns	V _{CC} = -10V, I _C = -1A, I _{B1} = I _{B2} = -100mA
	t _{OFF}	-	370	-		

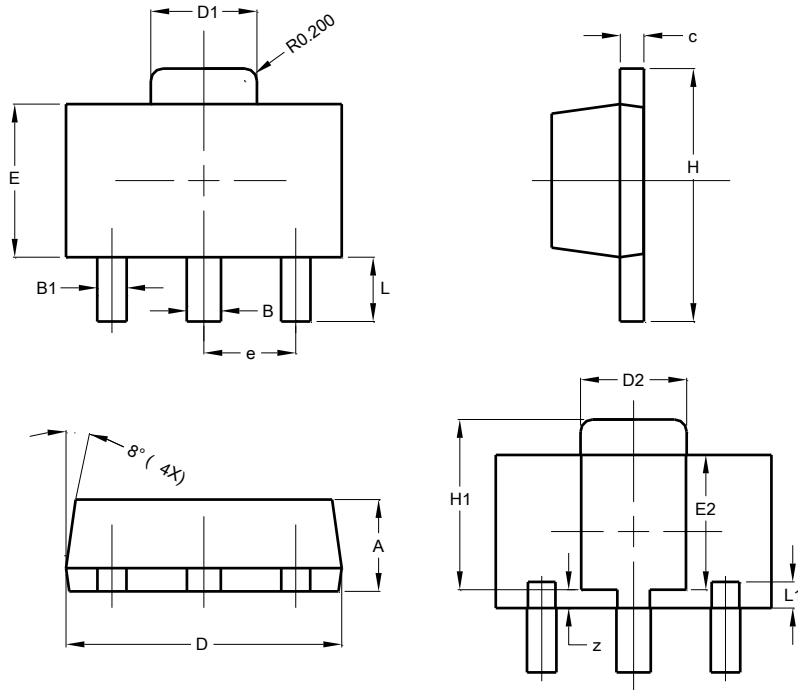
Notes: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



Package Outline Dimensions

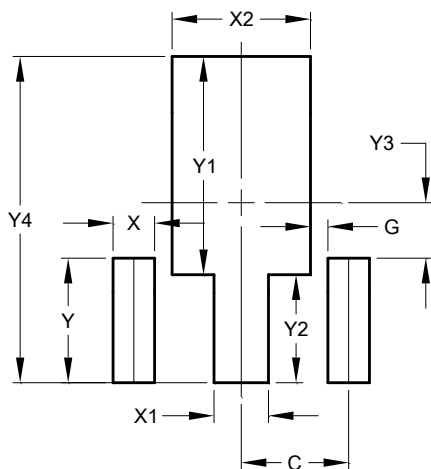
SOT89



SOT89			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

Suggested Pad Layout

SOT89



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530

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